NDD02N40, NDT02N40

N-Channel Power MOSFET 400 V, 5.5 Ω

Features

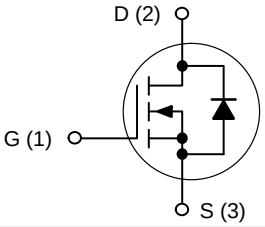
- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ON Semiconductor®

http://onsemi.com

$V_{(BR)DSS}$	$R_{DS(ON)}$ MAX
400 V	5.5 Ω @ 10 V

N−Channel MOSFET



ABSOLUTE MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter	Symbol	NDD	NDT	Unit
Drain−to−Source Voltage	V_{DSS}	400		V
Gate−to−Source Voltage	V_{GS}	±20		V
Continuous Drain Current $R_{\theta JC}$ Steady State, T_C = 25°C (Note 1)	I_D	1.7	0.4	A
Continuous Drain Current $R_{\theta JC}$ Steady State, T_C = 100°C (Note 1)	I_D	1.1	0.25	A
Power Dissipation – $R_{\theta JC}$ Steady State, T_C = 25°C	P_D	39	2.0	W
Pulsed Drain Current	I_{DM}	6.9	1.6	A
Continuous Source Current (Body Diode)	I_S	1.7	0.4	A
Single Pulse Drain−to−Source Avalanche Energy, I_D = 1 A	EAS	120		mJ
Maximum Temperature for Soldering Leads	T_L	260		°C
Operating Junction and Storage Temperature	T_J, T_{STG}	−55 to +150		°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

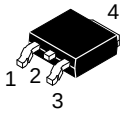
1. Limited by maximum junction temperature
2. I_S = 1.7 A, di/dt ≤ 100 A/μs, $V_{DD} \le BV_{DSS}$, T_J = +150°C

THERMAL RESISTANCE

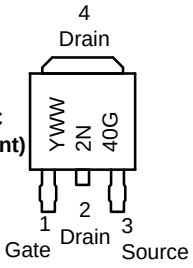
Parameter		Symbol	Value	Unit
Junction−to−Case (Drain)	NDD02N40	$R_{\theta JC}$	3.2	°C/W
Junction−to−Ambient Steady State		$R_{\theta JA}$		°C/W
	NDD02N40 (Note 4)		39	
	NDD02N40−1 (Note 3)		96	
	NDT02N40 (Note 4)		62	
	NDT02N40 (Note 5)		151	

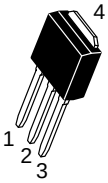
3. Insertion mounted
4. Surface mounted on FR4 board using 1″ sq. pad size (Cu area = 1.127″ sq. [2 oz] including traces)
5. Surface−mounted on FR4 board using minimum recommended pad size (Cu area = 0.026” sq. [2 oz]).

MARKING DIAGRAMS

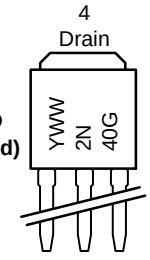


DPAK
CASE 369C
(Surface Mount)
STYLE 2



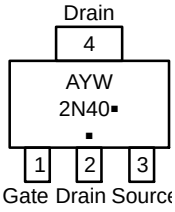


IPAK
CASE 369D
(Straight Lead)
STYLE 2



Y = Year
WW = Work Week
2N40 = Device Code
G = Pb−Free Package

SOT−223
CASE 318E
STYLE 3



A = Assembly Location
Y = Year
W = Work Week
2N40 = Specific Device Code
▪ = Pb−Free Package

(*Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 3 of this data sheet.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions		Min	Typ	Max	Unit
OFF CHARACTERISTICS							
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA		400			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$V_{(BR)DSS}/T_J$	Reference to 25°C, I_D = 1 mA			460		mV/°C
Drain−to−Source Leakage Current	I_{DSS}	V_{DS} = 400 V, V_{GS} = 0 V	T_J = 25°C			1	μA
			T_J = 125°C			50	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = ±20 V				±10	μA
ON CHARACTERISTICS (Note 6)							
Gate Threshold Voltage	$V_{GS(TH)}$	V_{DS} = V_{GS}, I_D = 250 μA		0.8	1.6	2	V
Negative Threshold Temperature Coefficient	$V_{GS(TH)}/T_J$	Reference to 25°C, I_D = 50 μA			4.6		mV/°C
Static Drain-to-Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 0.22 A			4.5	5.5	Ω
Forward Transconductance	g_{FS}	V_{DS} = 15 V, I_D = 0.22 A			1.1		S
DYNAMIC CHARACTERISTICS							
Input Capacitance (Note 7)	C_{iss}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz			121		pF
Output Capacitance (Note 7)	C_{oss}				16		
Reverse Transfer Capacitance (Note 7)	C_{rss}				3		
Total Gate Charge (Note 7)	Q_g	V_{DS} = 200 V, I_D = 1.7 A, V_{GS} = 10 V			5.5		nC
Gate-to-Source Charge (Note 7)	Q_{gs}				0.8		
Gate-to-Drain (“Miller”) Charge (Note 7)	Q_{gd}				1.0		
Plateau Voltage	V_{GP}				3.1		V
Gate Resistance	R_g				8.7		Ω
RESISTIVE SWITCHING CHARACTERISTICS (Note 8)							
Turn-on Delay Time	$t_{d(on)}$	V_{DD} = 200 V, I_D = 1.7 A, V_{GS} = 10 V, R_G = 0 Ω			5		ns
Rise Time	t_r				7		
Turn-off Delay Time	$t_{d(off)}$				14		
Fall Time	t_f				4		
SOURCE−DRAIN DIODE CHARACTERISTICS							
Diode Forward Voltage	V_{SD}	I_S = 1.7 A, V_{GS} = 0 V	T_J = 25°C		0.9	1.6	V
			T_J = 100°C		0.8		
Reverse Recovery Time	t_{rr}	V_{GS} = 0 V, V_{DD} = 30 V, I_S = 1.7 A, d_i/d_t = 100 A/μs			146		ns
Charge Time	t_a				37		
Discharge Time	t_b				109		
Reverse Recovery Charge	Q_{rr}				260		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

6. Pulse Width ≤ 380 μs, Duty Cycle ≤ 2%.
7. Guaranteed by design.
8. Switching characteristics are independent of operating junction temperatures.

ORDERING INFORMATION

Device	Package	Shipping†
NDD02N40−1G	IPAK (Pb−Free, Halogen Free)	75 Units / Rail
NDD02N40T4G	DPAK (Pb−Free, Halogen Free)	2500 / Tape & Reel
NDT02N40T1G	SOT−223 (Pb−Free, Halogen Free)	1000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

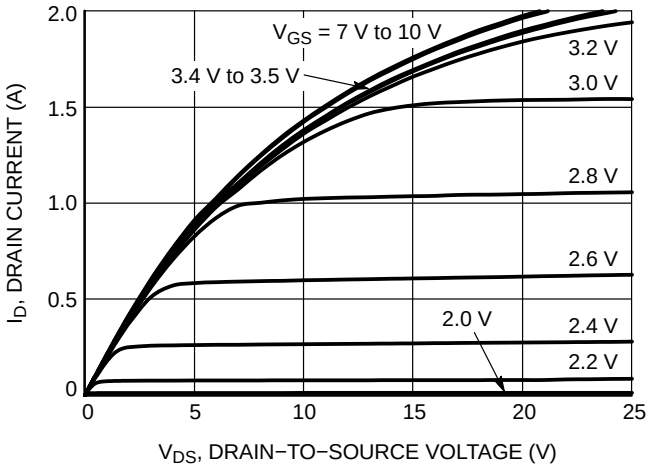


Figure 1. On−Region Characteristics

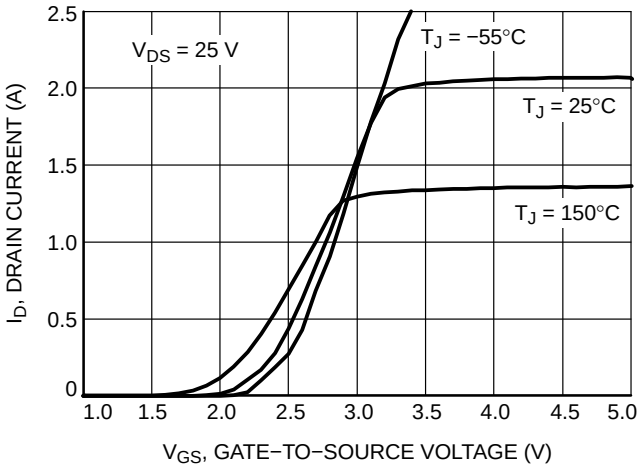


Figure 2. Transfer Characteristics

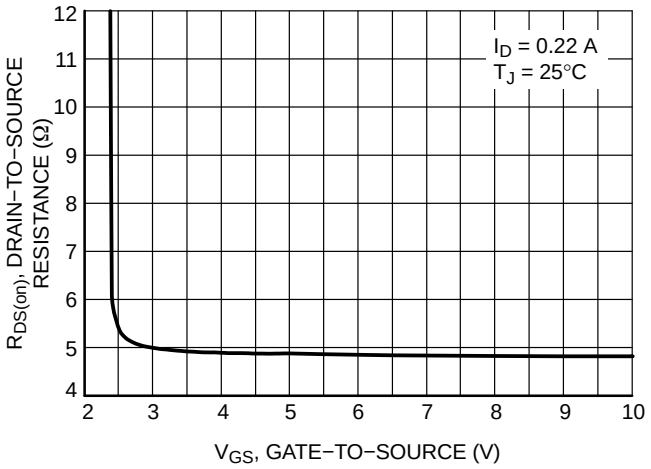


Figure 3. On−Resistance vs. Gate−to−Source Voltage

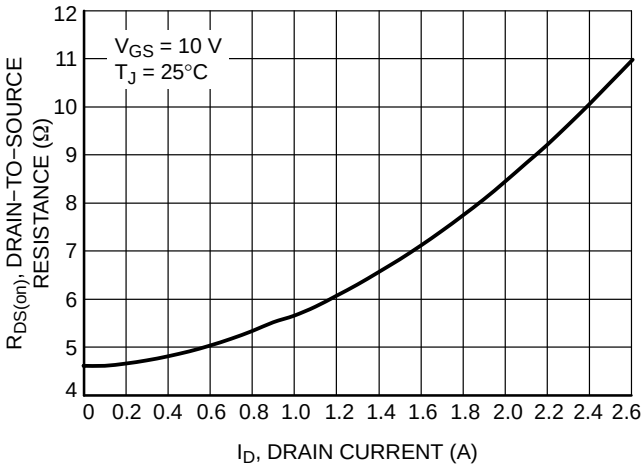


Figure 4. On−Resistance vs. Drain Current and Gate Voltage

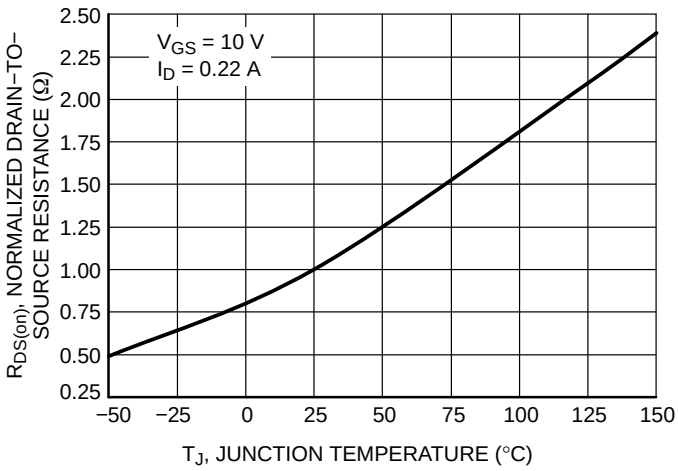


Figure 5. On−Resistance Variation with Temperature

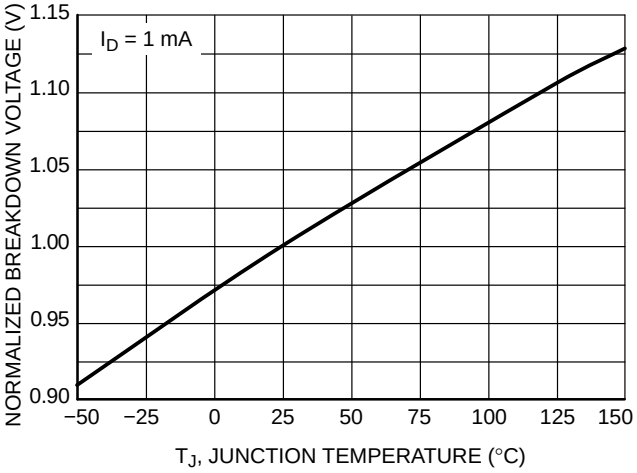


Figure 6. Normalized BVDSS with Temperature

TYPICAL CHARACTERISTICS

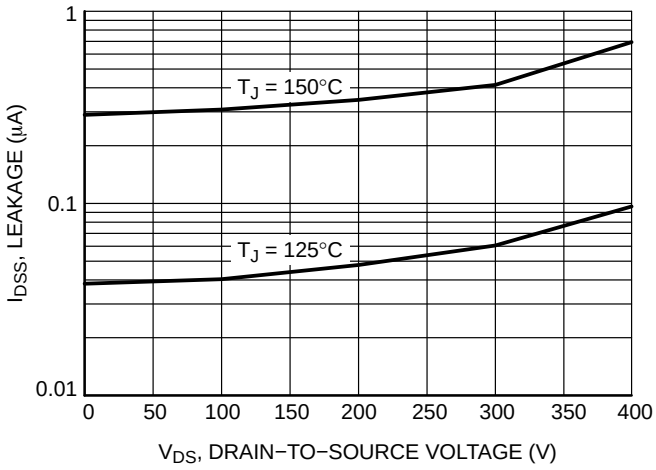


Figure 7. Drain−to−Source Leakage Current vs. Voltage

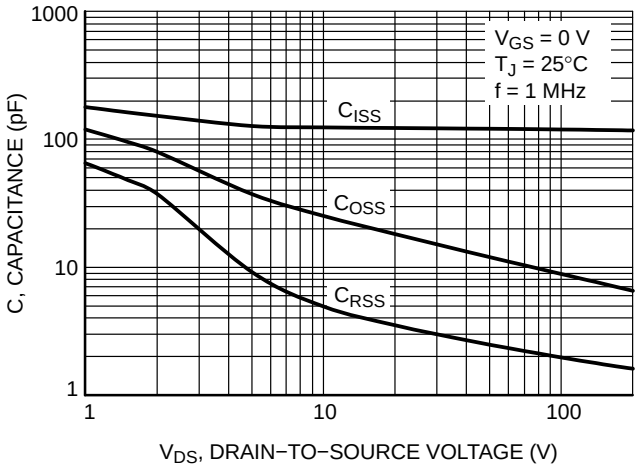


Figure 8. Capacitance Variation

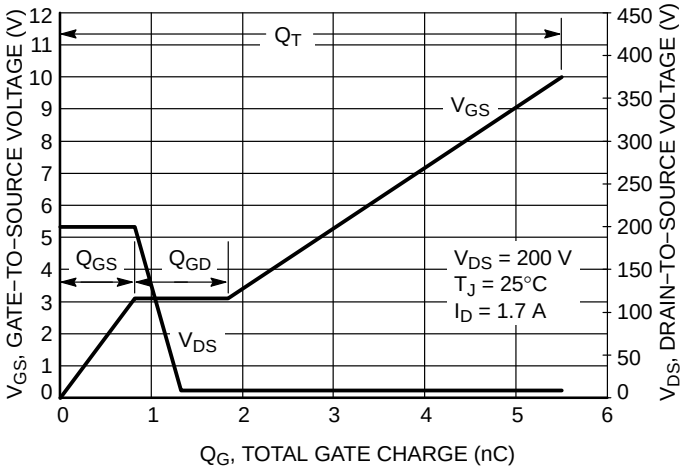


Figure 9. Gate−to−Source and Drain−to−Source Voltage vs. Total Charge

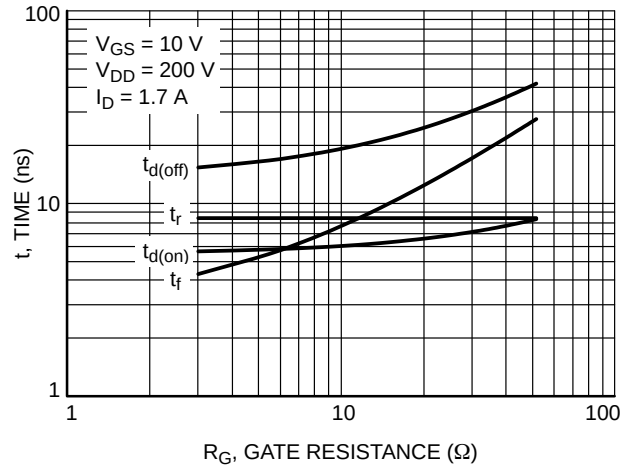


Figure 10. Resistive Switching Time Variation vs. Gate Resistance

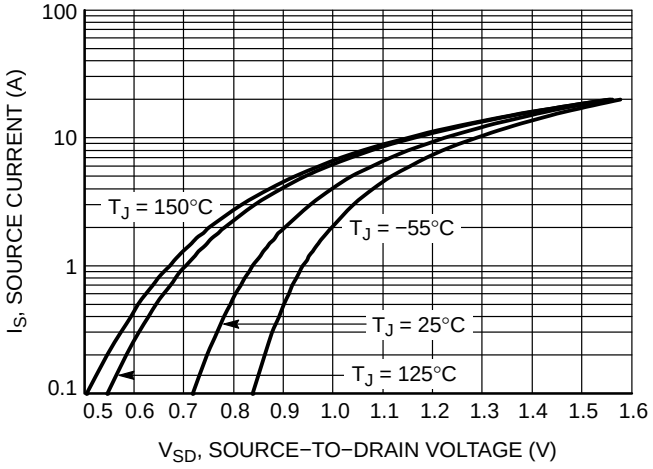


Figure 11. Diode Forward Voltage vs. Current

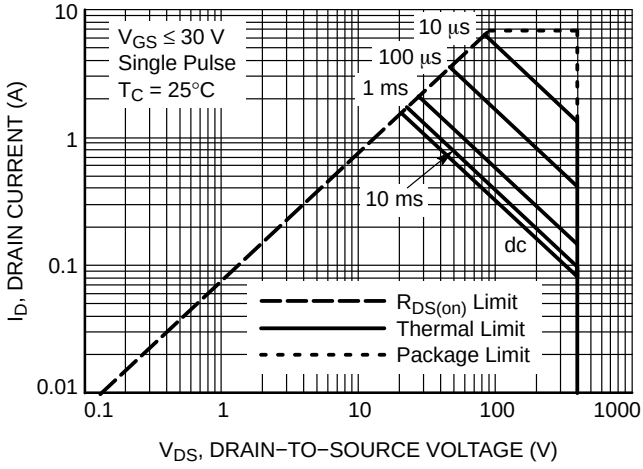


Figure 12. Maximum Rated Forward Biased Safe Operating Area for NDD02N40

TYPICAL CHARACTERISTICS

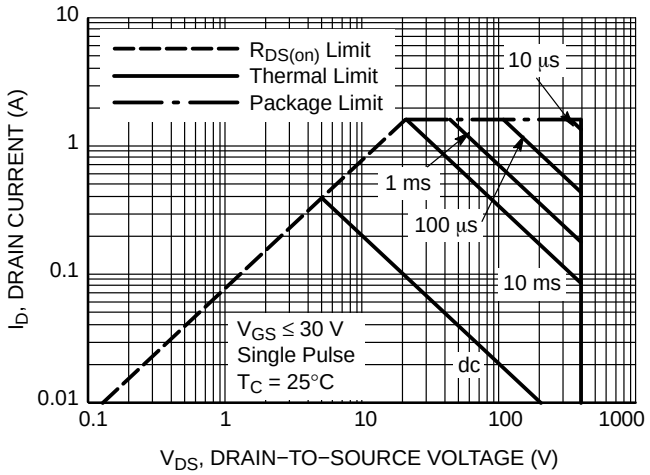


Figure 13. Maximum Rated Forward Biased Safe Operating Area for NDT02N40

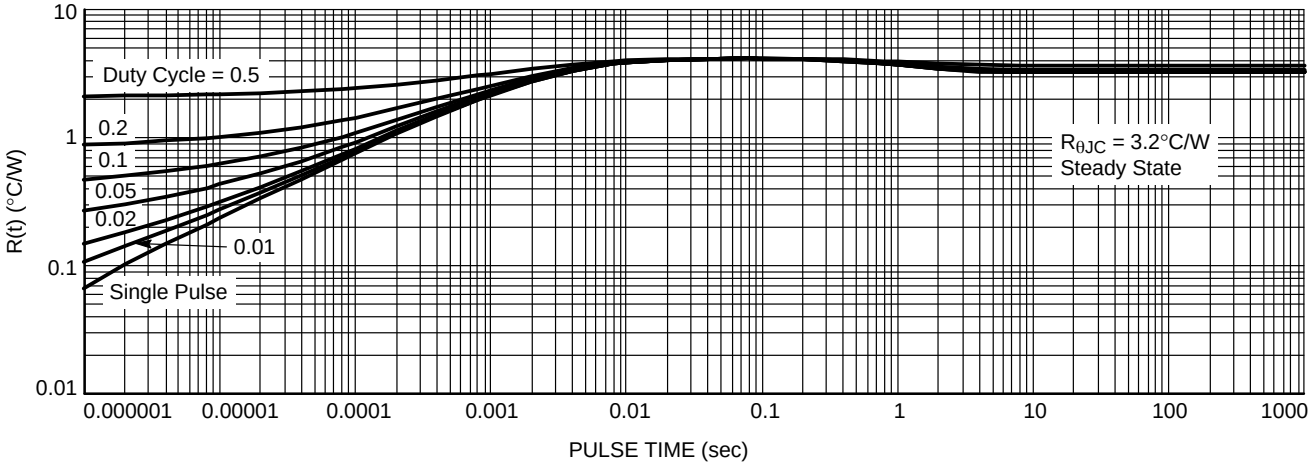


Figure 14. Thermal Impedance (Junction−to−Case) for NDD02N40

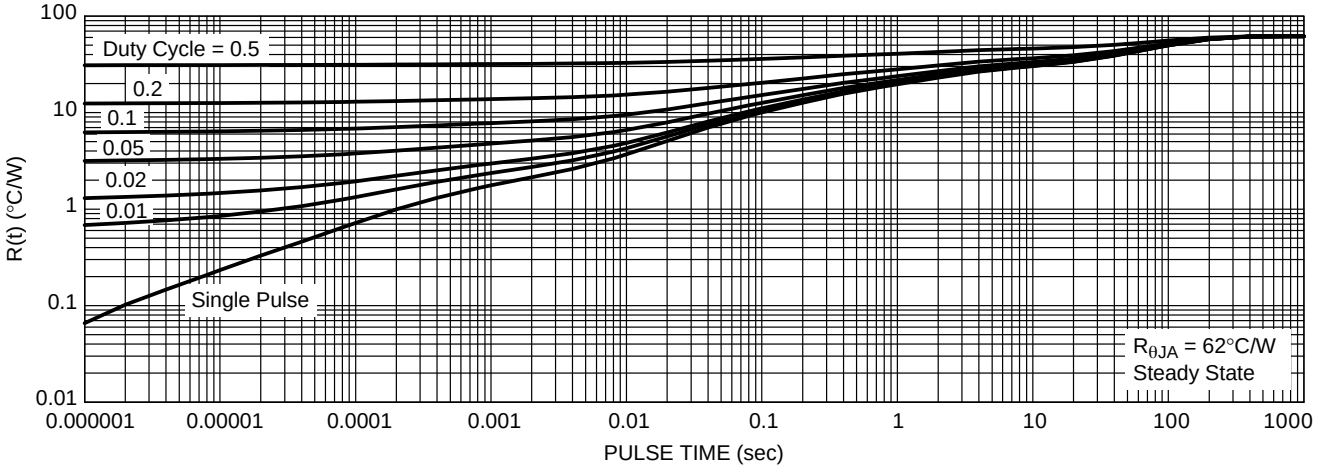
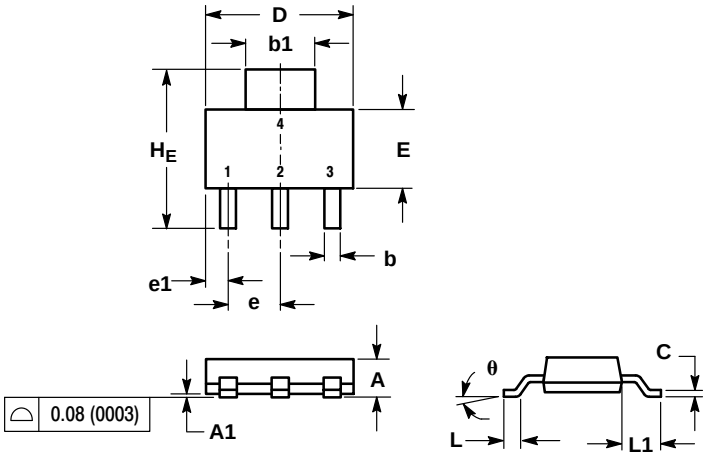


Figure 15. Thermal Impedance (Junction−to−Ambient) for NDT02N40

PACKAGE DIMENSIONS

SOT−223 (TO−261)
CASE 318E−04
ISSUE N

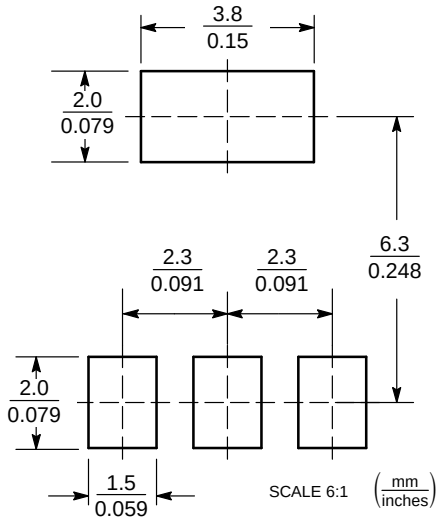


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCH.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
A	1.50	1.63	1.75	0.060	0.064	0.068
A1	0.02	0.06	0.10	0.001	0.002	0.004
b	0.60	0.75	0.89	0.024	0.030	0.035
b1	2.90	3.06	3.20	0.115	0.121	0.126
c	0.24	0.29	0.35	0.009	0.012	0.014
D	6.30	6.50	6.70	0.249	0.256	0.263
E	3.30	3.50	3.70	0.130	0.138	0.145
e	2.20	2.30	2.40	0.087	0.091	0.094
e1	0.85	0.94	1.05	0.033	0.037	0.041
L	0.20	−−−	−−−	0.008	−−−	−−−
L1	1.50	1.75	2.00	0.060	0.069	0.078
H_E	6.70	7.00	7.30	0.264	0.276	0.287
θ	0°	–	10°	0°	–	10°

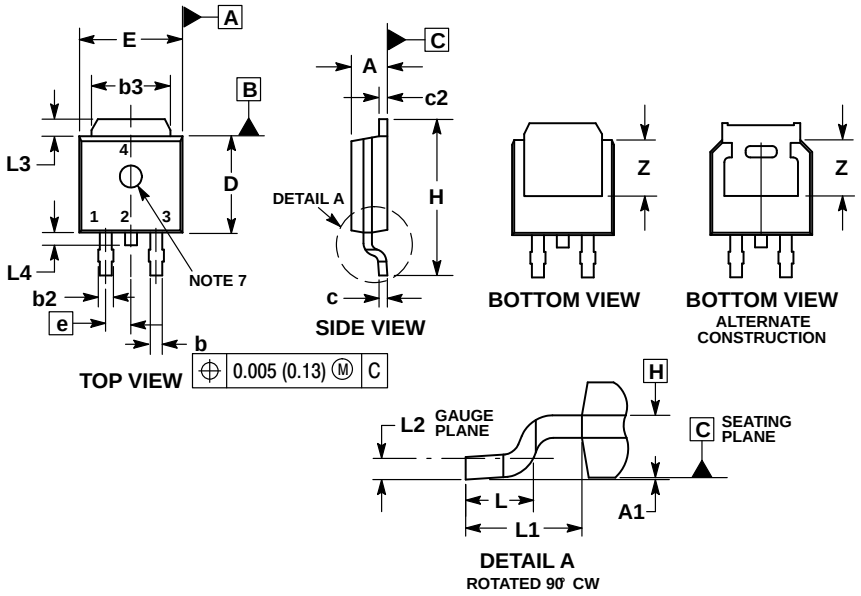
STYLE 3:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT



PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE)
CASE 369C
ISSUE E

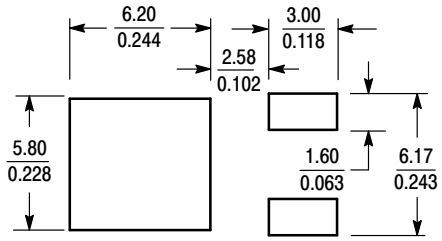


NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.
7. OPTIONAL MOLD FEATURE.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.028	0.045	0.72	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090 BSC		2.29 BSC	
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.114 REF		2.90 REF	
L2	0.020 BSC		0.51 BSC	
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*

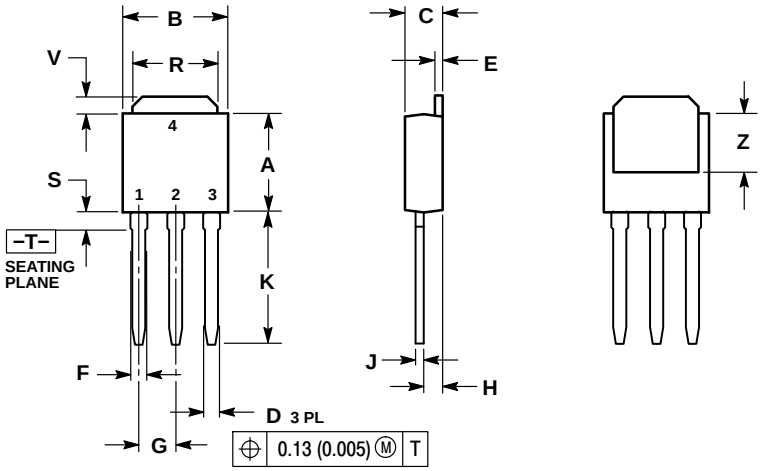


SCALE 3:1 (mm / inches)

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

PACKAGE DIMENSIONS

IPAK
CASE 369D
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	−−−	3.93	−−−

STYLE 2:
PIN 1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 5163, Denver, Colorado 80217 USA
Phone: 303−675−2175 or 800−344−3860 Toll Free USA/Canada
Fax: 303−675−2176 or 800−344−3867 Toll Free USA/Canada
Email: orderlit@onsemi.com

N. American Technical Support: 800−282−9855 Toll Free USA/Canada
Europe, Middle East and Africa Technical Support:
Phone: 421 33 790 2910
Japan Customer Focus Center
Phone: 81−3−5817−1050

ON Semiconductor Website: **www.onsemi.com**

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